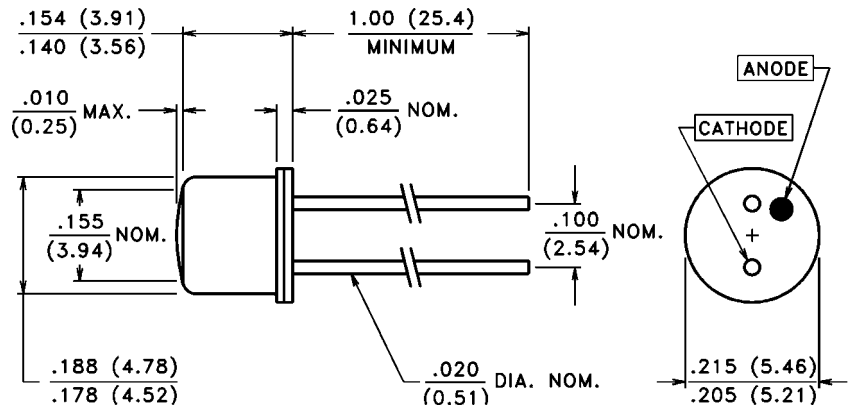




## PACKAGE DIMENSIONS inch (mm)



CASE 17 TO-46 HERMETIC  
CHIP ACTIVE AREA: .0025 in<sup>2</sup> (1.60 mm<sup>2</sup>)

## PRODUCT DESCRIPTION

Small area planar silicon photodiode in a "flat" window, dual lead TO-46 package. The package incorporates an infrared rejection filter. Cathode is common to the case. These diodes have very high shunt resistance and have good blue response.

## ABSOLUTE MAXIMUM RATINGS

Storage Temperature: -40°C to 110°C  
Operating Temperature: -40°C to 110°C

## ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTB curves, pages 21-22)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTB1012B			VTB1013B			UNITS
			Min.	Typ.	Max.	Min.	Typ.	Max.	
I <sub>SC</sub>	Short Circuit Current	H = 100 fc, 2850 K	0.8	1.3		0.8	1.3		μA
TC I <sub>SC</sub>	I <sub>SC</sub> Temperature Coefficient	2850 K		.02	.08		.02	.08	%/°C
V <sub>OC</sub>	Open Circuit Voltage	H = 100 fc, 2850 K		420			420		mV
TC V <sub>OC</sub>	V <sub>OC</sub> Temperature Coefficient	2850 K		-2.0			-2.0		mV/°C
I <sub>D</sub>	Dark Current	H = 0, VR = 2.0 V			100			20	pA
R <sub>SH</sub>	Shunt Resistance	H = 0, V = 10 mV		.25			7.0		GΩ
TC R <sub>SH</sub>	R <sub>SH</sub> Temperature Coefficient	H = 0, V = 10 mV		-8.0			-8.0		%/°C
C <sub>J</sub>	Junction Capacitance	H = 0, V = 0		.31			.31		nF
λ <sub>range</sub>	Spectral Application Range		330		720	330		720	nm
λ <sub>p</sub>	Spectral Response - Peak			580			580		nm
V <sub>BR</sub>	Breakdown Voltage		2	40		2	40		V
θ <sub>1/2</sub>	Angular Resp. - 50% Resp. Pt.			±35			±35		Degrees
NEP	Noise Equivalent Power		5.3 x 10 <sup>-14</sup> (Typ.)			1.1 x 10 <sup>-14</sup> (Typ.)			W/√Hz
D*	Specific Detectivity		2.4 x 10 <sup>12</sup> (Typ.)			1.2 x 10 <sup>13</sup> (Typ.)			cm√Hz / W